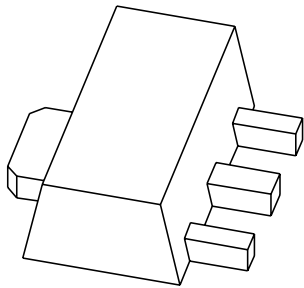


DATA SHEET



BST15; BST16 PNP high-voltage transistors

Product specification
Supersedes data of 1999 Apr 26

2004 Dec 14

PNP high-voltage transistors

BST15; BST16

FEATURES

- Low current (max. 200 mA)
- High voltage (max. 300 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

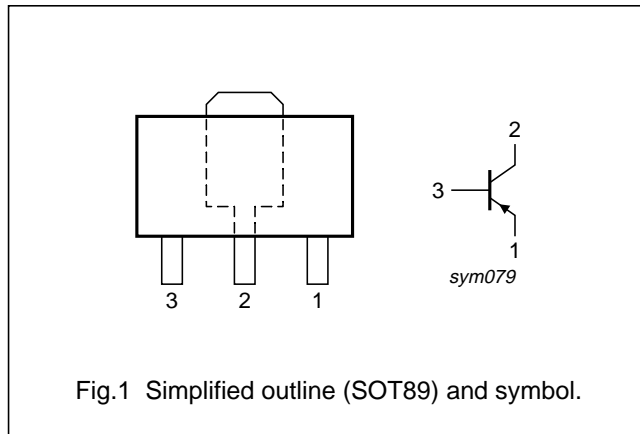
PNP high-voltage transistor in a SOT89 plastic package.
NPN complements: BST39 and BST40.

MARKING

TYPE NUMBER	MARKING CODE
BST15	BT1
BST16	BT2

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BST15	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89
BST16			

PNP high-voltage transistors

BST15; BST16

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BST15		–	–200	V
	BST16		–	–350	V
V _{CEO}	collector-emitter voltage	open base			
	BST15		–	–200	V
	BST16		–	–300	V
V _{EBO}	emitter-base voltage	open collector			
	BST15		–	–4	V
	BST16		–	–6	V
I _C	collector current (DC)		–	–200	mA
I _{CM}	peak collector current		–	–400	mA
I _{BM}	peak base current		–	–200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	1.3	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	ambient temperature		–65	+150	°C

Note

- Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm².
For other mounting conditions, see “*Thermal considerations for SOT89 in the General Part of associated Handbook*”.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	95	K/W
R _{th(j-s)}	thermal resistance from junction to soldering point		15	K/W

Note

- Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm².
For other mounting conditions, see “*Thermal considerations for SOT89 in the General Part of associated Handbook*”.

PNP high-voltage transistors

BST15; BST16

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current				
	BST15	$I_E = 0\text{ A}; V_{CB} = -175\text{ V}$	–	–100	nA
	BST16	$I_E = 0\text{ A}; V_{CB} = -280\text{ V}$	–	–100	nA
I_{EBO}	emitter-base cut-off current				
	BST15	$I_C = 0\text{ A}; V_{EB} = -4\text{ V}$	–	–100	nA
	BST16	$I_C = 0\text{ A}; V_{EB} = -6\text{ V}$	–	–100	nA
h_{FE}	DC current gain	$I_C = -50\text{ mA}; V_{CE} = -10\text{ V}$			
	BST15		30	150	
	BST16		30	120	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	–	750	mV
C_c	collector capacitance	$I_E = i_e = 0\text{ A}; V_{CB} = -10\text{ V};$ $f = 1\text{ MHz}$	–	15	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -10\text{ V};$ $f = 100\text{ MHz}$	15	–	MHz

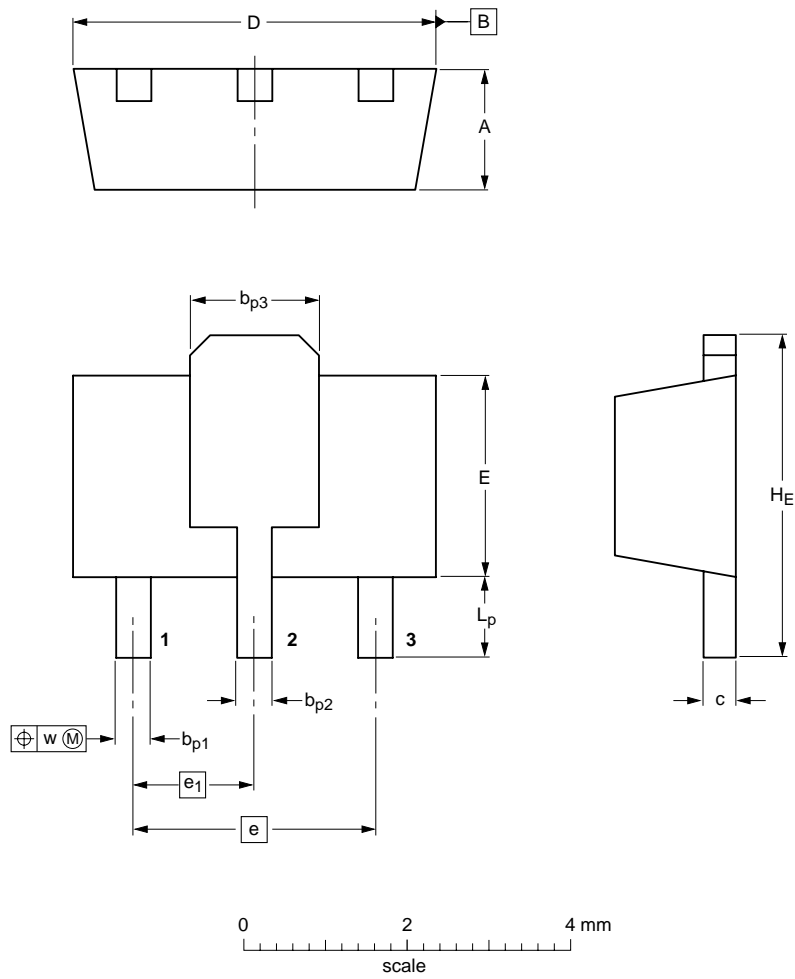
PNP high-voltage transistors

BST15; BST16

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	bp1	bp2	bp3	c	D	E	e	e1	HE	Lp	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT89		TO-243	SC-62		99-09-13 04-08-03

PNP high-voltage transistors

BST15; BST16

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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